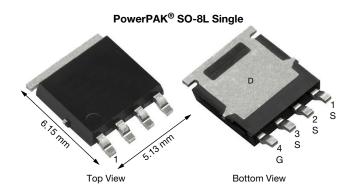


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Vishay Siliconix

# Automotive N-Channel 80 V (D-S) 175 °C MOSFET



PRODUCT SUMMARY	
V <sub>DS</sub> (V)	80
$R_{DS(on)}$ ( $\Omega$ ) at $V_{GS} = 10 \text{ V}$	0.0095
I <sub>D</sub> (A)	57
Configuration	Single
Package	PowerPAK SO-8L

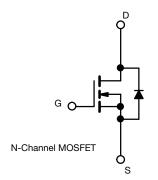
#### **FEATURES**

- TrenchFET® power MOSFET
- AEC-Q101 qualified
- 100 % Rq and UIS tested
- Material categorization: for definitions of compliance please see www.vishav.com/doc?99912





ROHS COMPLIANT HALOGEN FREE



PARAMETER	SYMBOL	LIMIT	UNIT		
Drain-source voltage	V <sub>DS</sub>	80	V		
Gate-source voltage	$V_{GS}$	± 20	V		
Continuous drain current	T <sub>C</sub> = 25 °C	1	57		
	T <sub>C</sub> = 125 °C	I <sub>D</sub>	33		
Continuous source current (diode conduction)	I <sub>S</sub>	60	А		
Pulsed drain current <sup>a</sup>		I <sub>DM</sub>		150	
Single pulse avalanche current	L = 0.1 mH	I <sub>AS</sub>	33		
Single pulse avalanche energy	L=0.1 min	E <sub>AS</sub>	54	mJ	
Maximum power dissipation <sup>a</sup>	T <sub>C</sub> = 25 °C	D	68	W	
	T <sub>C</sub> = 125 °C	$P_{D}$	22		
Operating junction and storage temperature range		T <sub>J</sub> , T <sub>stg</sub>	-55 to +175	%0	
Soldering recommendations (peak temperature) c, d			260	°C	

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-ambient P	CB mount b	$R_{thJA}$	68	°C/W
Junction-to-case (drain)		$R_{thJC}$	2.2	G/VV

#### Notes

- a. Pulse test; pulse width  $\leq$  300  $\mu$ s, duty cycle  $\leq$  2 %.
- b. When mounted on 1" square PCB (FR4 material).
- c. See solder profile (<u>www.vishay.com/doc?73257</u>). The PowerPAK SO-8L is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- d. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.

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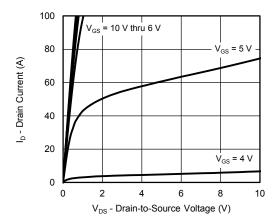
PARAMETER	SYMBOL	TES	T CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static				'	•		L
Drain-source breakdown voltage	V <sub>DS</sub>	$V_{GS} = 0$ , $I_D = 250 \mu A$		80	-	-	V
Gate-source threshold voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =	· V <sub>GS</sub> , I <sub>D</sub> = 250 μA	2.5	3.0	3.5	V
Gate-source leakage	I <sub>GSS</sub>	V <sub>DS</sub> =	0 V, V <sub>GS</sub> = ± 20 V	-	-	± 100	nA
		V <sub>GS</sub> = 0 V	V <sub>DS</sub> = 80 V	-	-	1	
Zero gate voltage drain current	I <sub>DSS</sub>	V <sub>GS</sub> = 0 V	V <sub>DS</sub> = 80 V, T <sub>J</sub> = 125 °C	-	-	50	μΑ
		V <sub>GS</sub> = 0 V	V <sub>DS</sub> = 80 V, T <sub>J</sub> = 175 °C	-	-	150	
On-state drain current a	I <sub>D(on)</sub>	V <sub>GS</sub> = 10 V	$V_{DS} \ge 5 \text{ V}$	30	-	-	Α
	_(=:-,	V <sub>GS</sub> = 10 V	I <sub>D</sub> = 10 A	-	0.0078	0.0095	Ω
Drain-source on-state resistance a	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V	I <sub>D</sub> = 10 A, T <sub>J</sub> = 125 °C	-	-	0.0152	
	- (- )	V <sub>GS</sub> = 10 V	I <sub>D</sub> = 10 A, T <sub>J</sub> = 175 °C	-	_	0.0188	
Forward transconductance b		V <sub>DS</sub>	= 15 V, I <sub>D</sub> = 10 A	-	36	-	S
Dynamic <sup>b</sup>				l			<u>l</u>
Input capacitance	C <sub>iss</sub>	T		-	2005	2650	
Output capacitance	C <sub>oss</sub>	V <sub>GS</sub> = 0 V	V <sub>DS</sub> = 25 V, f = 1 MHz	_	1055	1400	pF
Reverse transfer capacitance	C <sub>rss</sub>	1		-	36	50	
Total gate charge <sup>c</sup>	Qg			-	30	45	
Gate-source charge <sup>c</sup>	Q <sub>gs</sub>	V <sub>GS</sub> = 10 V	$V_{DS} = 40 \text{ V}, I_{D} = 5 \text{ A}$	_	9	-	nC
Gate-drain charge c	Q <sub>gd</sub>	1		_	5	-	
Gate resistance	R <sub>g</sub>		f = 1 MHz	0.20	0.45	0.68	Ω
Turn-on delay time <sup>c</sup>	t <sub>d(on)</sub>	$V_{DD}=40~V,~R_L=8~\Omega$ $I_D\cong 5~A,~V_{GEN}=10~V,~R_g=1~\Omega$		-	15	25	ns
Rise time <sup>c</sup>	t <sub>r</sub>			-	5	10	
Turn-off delay time <sup>c</sup>	t <sub>d(off)</sub>			-	24	40	
Fall time <sup>c</sup>	t <sub>f</sub>			-	14	25	
Source-Drain Diode Ratings and Charac	teristics b			l			L
Pulsed current <sup>a</sup>	I <sub>SM</sub>			_	_	150	Α
Forward voltage	V <sub>SD</sub>	l <sub>F</sub> :	= 10 A, V <sub>GS</sub> = 0	-	0.8	1.2	V
Body diode reverse recovery time	t <sub>rr</sub>	<u> </u>		-	57	115	ns
Body diode reverse recovery charge	Q <sub>rr</sub>	1	A -1:/-1+ 100 A/	-	88	180	nC
Reverse recovery fall time	t <sub>a</sub>	I <sub>F</sub> = 10	A, di/dt = 100 A/μs	-	27	-	no
Reverse recovery rise time	t <sub>b</sub>			-	31	-	ns
Body diode peak reverse recovery current	I <sub>RM(REC)</sub>			-	-2.9	-6	Α

#### **Notes**

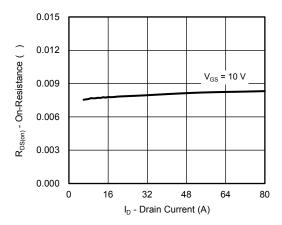
- a. Pulse test; pulse width  $\leq$  300  $\mu$ s, duty cycle  $\leq$  2 %.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

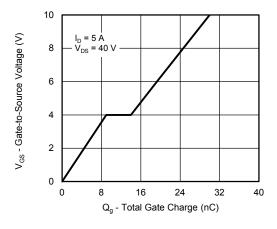




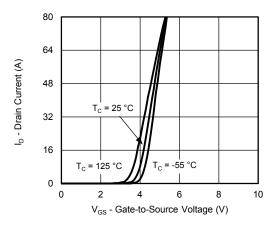
#### **Output Characteristics**



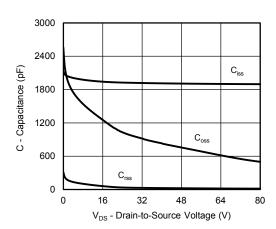
On-Resistance vs. Drain Current



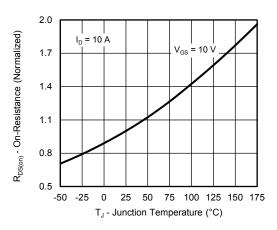
**Gate Charge** 



**Transfer Characteristics** 

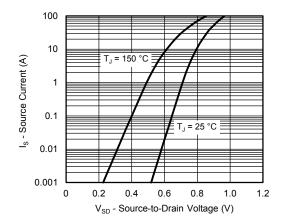


Capacitance

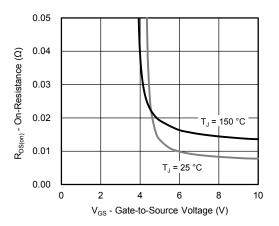


On-Resistance vs. Junction Temperature

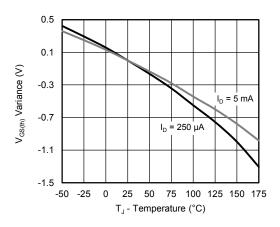




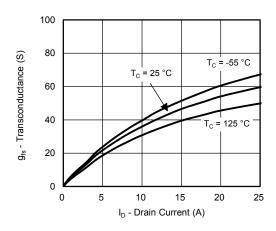
**Source Drain Diode Forward Voltage** 



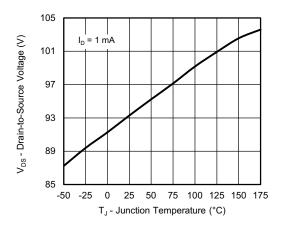
On-Resistance vs. Gate-to Source Voltage



**Threshold Voltage** 

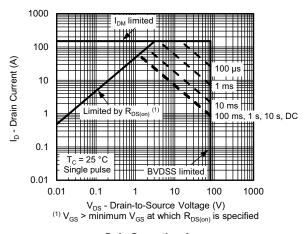


Transconductance

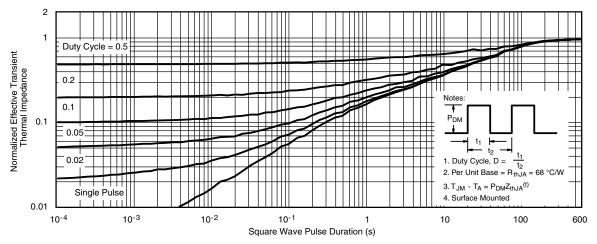


**Drain Source Breakdown vs. Junction Temperature** 



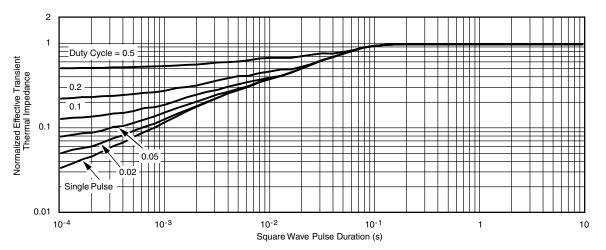


Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient





Normalized Thermal Transient Impedance, Junction-to-Case

#### Note

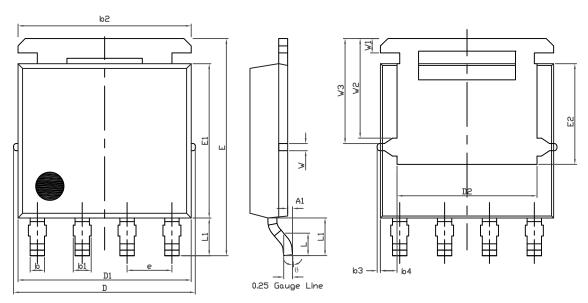
- The characteristics shown in the two graphs
  - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
  - Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

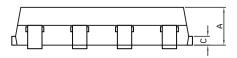
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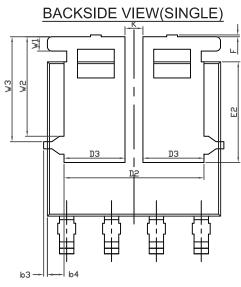


# PowerPAK® SO-8L Case Outline 2



**TOPSIDE VIEW** 





BACKSIDE VIEW(DUAL)



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DIM		MILLIMETERS		INCHES			
DIM.	MIN.	NOM.	MAX.	MIN. NOM.		MAX.	
Α	1.00	1.07	1.14	0.039	0.042	0.045	
A1	0.00	-	0.127	0.00	-	0.005	
b	0.33	0.41	0.48	0.013	0.016	0.019	
b1	0.44	0.51	0.58	0.017	0.020	0.023	
b2	4.80	4.90	5.00	0.189	0.193	0.197	
b3		0.094		0.004			
b4		0.47			0.019		
С	0.20	0.25	0.30	0.008	0.010	0.012	
D	5.00	5.13	5.25	0.197	0.202	0.207	
D1	4.80	4.90	5.00	0.189	0.193	0.197	
D2	3.86	3.96	4.06	0.152	0.156	0.160	
D3	1.63	1.73	1.83	0.064	0.068	0.072	
е		1.27 BSC		0.050 BSC			
Е	6.05	6.15	6.25	0.238	0.242	0.246	
E1	4.27	4.37	4.47	0.168	0.172	0.176	
E2	2.75	2.85	2.95	0.108	0.112	0.116	
F	-	-	0.15	-	-	0.006	
L	0.62	0.72	0.82	0.024	0.028	0.032	
L1	0.92	1.07	1.22	0.036	0.042	0.048	
K		0.51			0.020		
W	0.23				0.009		
W1	0.41			0.016			
W2	2.82			0.111			
W3	2.96			2.96 0.117			
q	0°	-	10°	0°	-	10°	

ECN: S19-0643-Rev. B, 05-Aug-2019

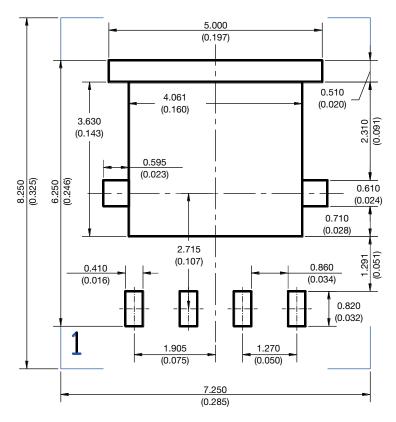
DWG: 6044

### Note

• Millimeters will gover



### RECOMMENDED MINIMUM PAD FOR PowerPAK® SO-8L SINGLE



Recommended Minimum Pads Dimensions in mm (inches)



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